

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Not for submission under 37 CFR 1.99)</i>		Application Number		10595283	
		Filing Date		2004-09-16	
		First Named Inventor		Bocang QIU	
		Art Unit			
		Examiner Name			
		Attorney Docket Number		305832-00124	

Examiner Initial*	Cite No	Foreign Document Number ³	Country Code ² <i>i</i>	Kind Code ⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear	T5
<i>QH</i>	1	61-156788	JP	A1	07/1986		translation of abstract only	<input checked="" type="checkbox"/>

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<i>QH</i>	1	WENZEL, H. et al., "High-power diode lasers with small vertical beam divergence emitting at 808nm", ELECTRONICS LETTERS, Vol. 37, No. 16, pp. 1024-1026 (August 2, 2001), Great Britain	<input type="checkbox"/>
	2	NAYAR, B. K. et al., "Novel high-power narrow-beam divergence tapered laser arrays at 980 nm", TECHNICAL DIGEST, CONFERENCE ON LASERS AND ELECTRO-OPTICS, San Francisco, CA, May 3, 1988, pp. 39 - 40	<input type="checkbox"/>
	3	VAKHSHOORI, D. et al., "980 nm spread index laser with strain compensated InGaAs/GaAsP/InGaP and 90% fibre coupling efficiency", ELECTRONICS LETTERS Vol. 32, No. 11, May 23, 1996, pp. 1007-1008, Great Britain	<input type="checkbox"/>
	4	LAY, T.S. et al., "Electro-modulation spectroscopy and laser performance of an InGaAsP asymmetric multi-quantum-well structure", OPTICS COMMUNICATIONS, Vol. 211, No. 1 - 6, October 1, 2002, pp. 289-294, North-Holland Publishing Co., Amsterdam, Netherlands	<input type="checkbox"/>
	5	BUDA, M. et al., "Asymmetric design of semiconductor laser diodes: thin p-clad and low divergence InGaAs/AlGaAs/GaAs devices", 15TH ANNUAL MEETING OF THE IEEE LASERS AND ELECTRO-OPTICS SOCIETY, Vol. 1 of 2, pp. 647 - 648, Glasgow, Scotland, Nov. 13, 2002	<input type="checkbox"/>
	6	SMOWTON, P. M., et al., '650 nm lasers with narrow far-field divergence with integrated optical mode expansion layers", IEEE J. OF SELECTED TOPICS IN QUANTUM ELECTRONICS, Vol. 5, No. 3, May 1999, pp. 735 - 739	<input type="checkbox"/>
<i>V</i>	7	EUROPEAN PATENT OFFICE acting as the IPSA, Written Opinion in Appln. No. PCT/GB2004/003959, issued 18 April 2006	<input type="checkbox"/>

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	2	4794611	A1	1988-12-27	Canon KK	
	3	5923689	A	1999-07-13	Su et al.	
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OR	2	20040047378	A1	2004-03-11	Erbert et al.	

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